Carrier relaxation mechanisms in self-assembled (In,Ga)As/GaAs quantum dots: Efficient $P \rightarrow S$ Auger relaxation of electrons

A. [illegible],* B. [illegible], A. [illegible]

[illegible] 8 [illegible] 2006; [illegible] 1 A[illegible] 2006

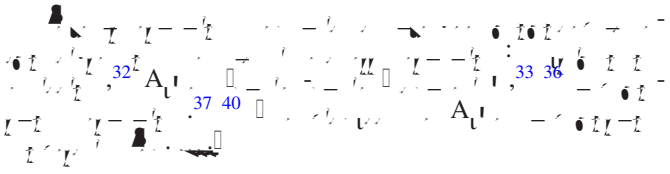
[illegible]

II. CHARACTERISTIC DYNAMICAL PROCESSES OF EXCITED ELECTRONS AND HOLES IN SELF-ASSEMBLED (In,Ga)As/GaAs QUANTUM DOTS

A. Barrier-to-wetting layer carrier capture

B. Carrier capture from the wetting layer into the dot

C. Relaxation of excited carriers within the dot



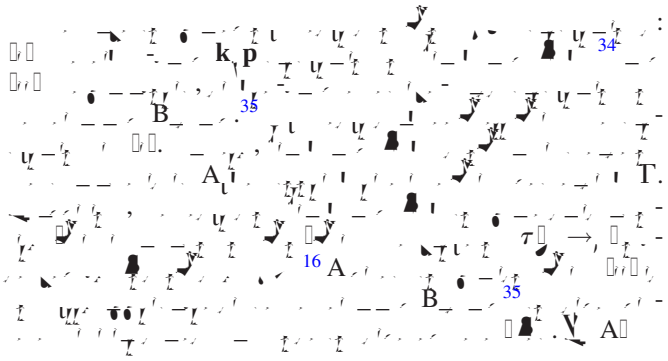
R ,α [52]

E . 1 , ψ B

,k R A , A ,

k ε: [53]

D. Comparison to other calculations for (In,Ga)As/GaAs dots



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